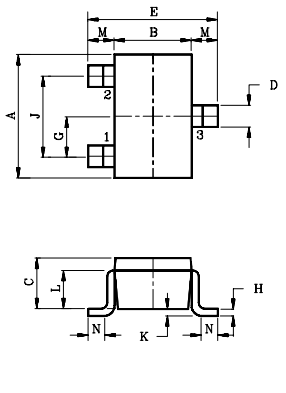
KTC4076

EPITAXIAL PLANAR NPN TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEAUTRES

- Excellent h_{FE} Linearity : $h_{FE}(2)$=25(Min.) at V_{CE}=6V, I_C=400mA.
- Complementary to KTA2015.

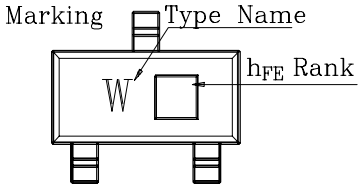


DIM	MILLIMETERS
A	2.00±0.20
B	1.25±0.15
C	0.90±0.10
D	0.3+0.10/−0.05
E	2.10±0.20
G	0.65
H	0.15+0.1/−0.06
J	1.30
K	0.00−0.10
L	0.70
M	0.42±0.10
N	0.2 MIN

USM

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	500	mA
Base Current	I_B	50	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=35V, I_E=0	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	0.1	μA
DC Current Gain (Note)	$h_{FE}(1)$	V_{CE}=1V, I_C=100mA	70	-	240	
	$h_{FE}(2)$	V_{CE}=6V, I_C=400mA	25	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=100mA, I_B=10mA	-	0.1	0.25	V
Base-Emitter Voltage	V_{BE}	V_{CE}=1V, I_C=100mA	-	0.8	1.0	V
Transition Frequency	f_T	V_{CE}=6V, I_C=20mA	-	300	-	MHz
Collector Output Capacitance	C_{ob}	V_{CE}=6V, I_E=0, f=1MHz	-	7.0	-	pF

Note) $h_{FE}(1)$ Classification O(2) : 70~140, Y(4) : 120~240
$h_{FE}(2)$ Classification O : 25Min, Y : 40Min.